

Silicon Epitaxial Planar Transistor(NPN)

Features

High Collector Current
 Complementary To MMBT3906
 Excellent HFE Linearity



Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	200	mA
P _C	Collector Dissipation	200	mW
T _J , T _{stg}	Junction and Storage Temperature	-55~150	°C

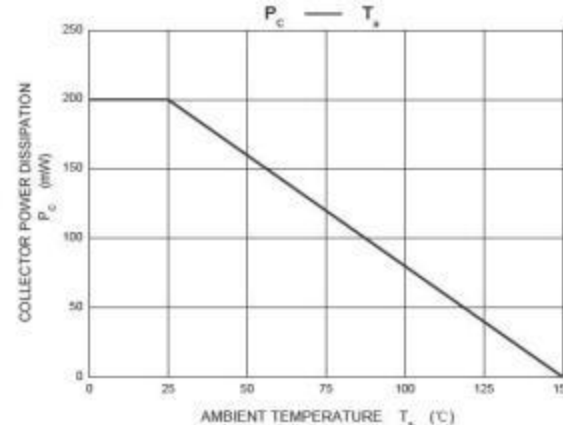
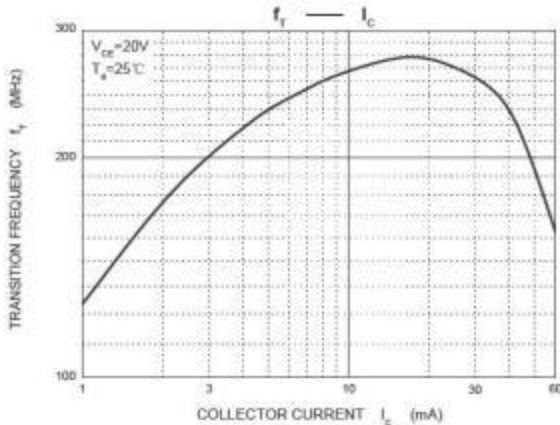
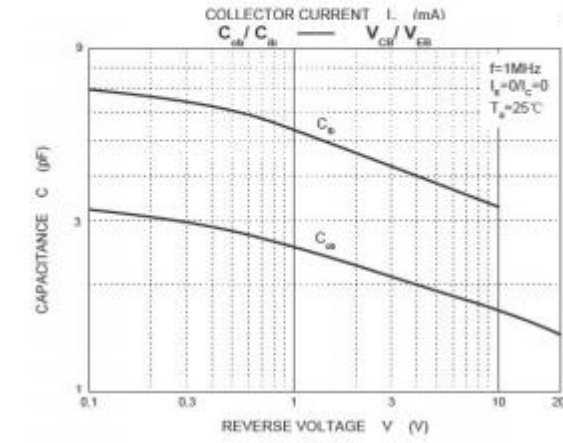
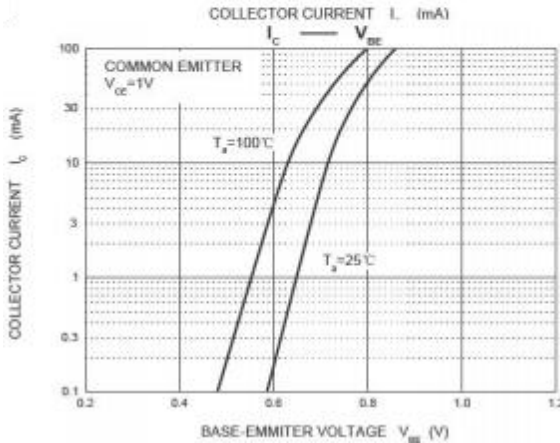
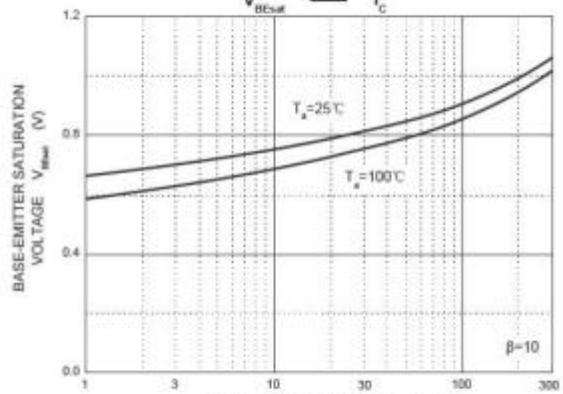
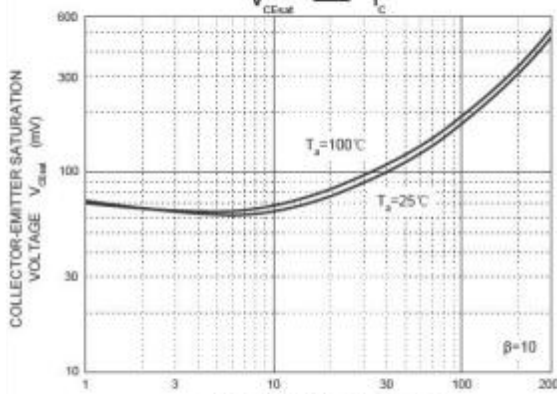
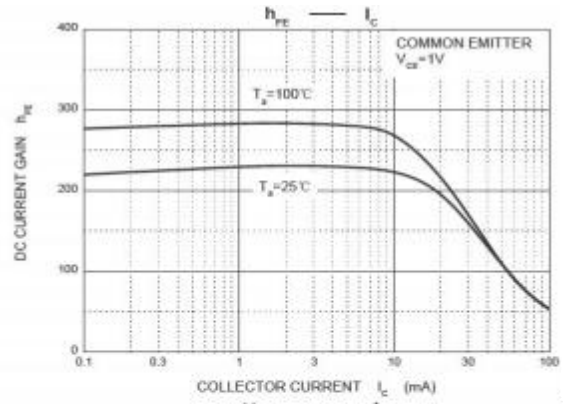
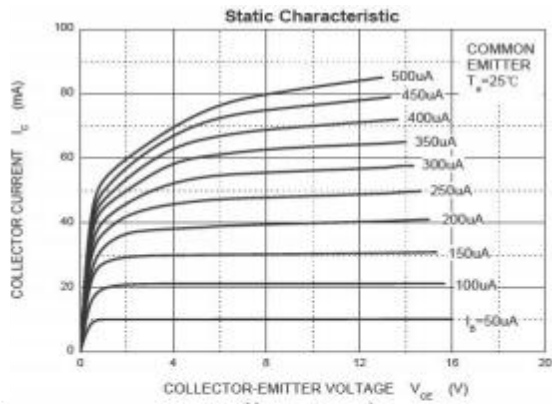
Electrical Characteristics T_A = 25°C unless otherwise noted

Parameter	Symbols	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	60		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	40		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6		V
Collector cut-off current	I _{CEX}	V _{CE} =30V, V _{EB(off)} =3V		50	nA
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0		100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		100	nA
DC current gain	h _{FE} (1)	V _{CE} =1V, I _C =10mA	100	300	
	h _{FE} (2)	V _{CE} =1V, I _C =50mA	60		
	h _{FE} (3)	V _{CE} =1V, I _C =100mA	30		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA		0.30	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =50mA, I _B =5mA		0.95	V
Transition frequency	f _T	V _{CE} =20V, I _C =10mA, f=100MHz	300		MHz
Delay time	t _d	V _{CC} =3V, V _{BE(off)} =-0.5V, I _C =10mA, I _{B1} =1mA		35	nS
Rise time	t _r	V _{CC} =3V, V _{BE(off)} =-0.5V, I _C =10mA, I _{B1} =1mA		35	nS
Storage time	t _s	V _{CC} =3V, I _C =10mA, I _{B1} =I _{B2} =1mA		200	nS
Fall time	t _f	V _{CC} =3V, I _C =10mA, I _{B1} =I _{B2} =1mA		50	nS

Device Information

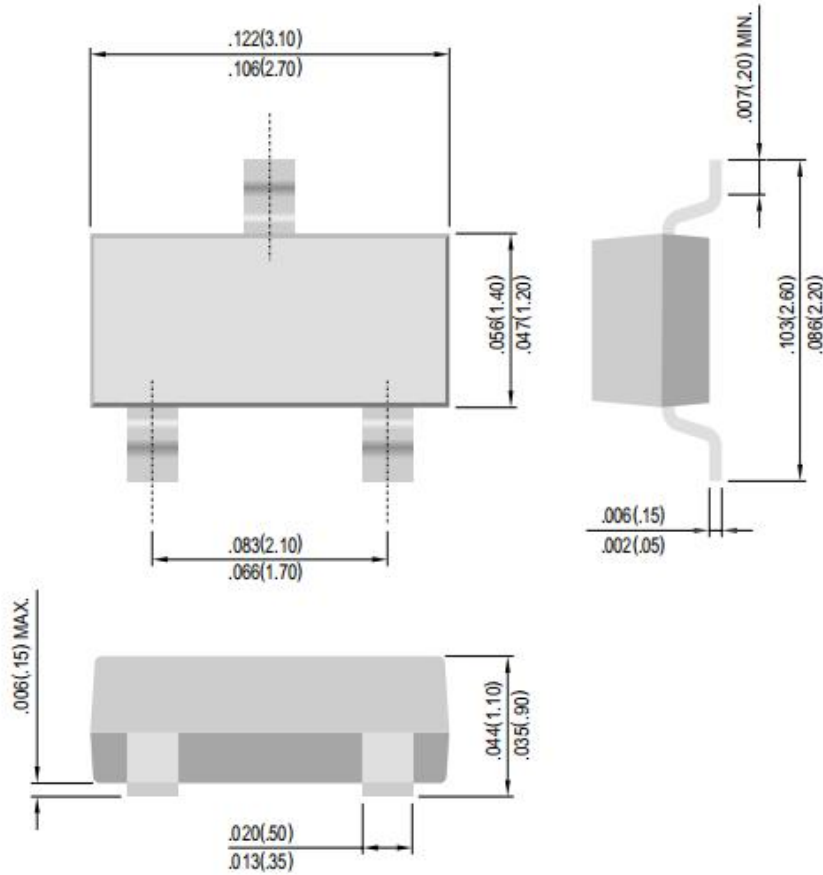
Type	MMBT3904
Marking	1AM
HFE	100-300

Typical Characteristics



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